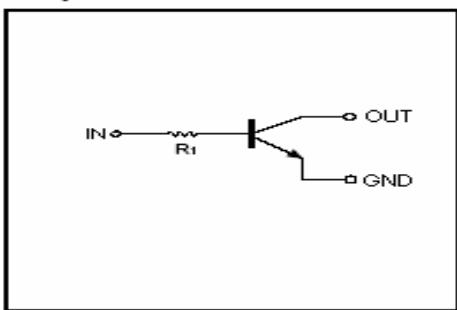


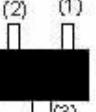
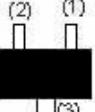
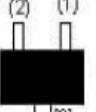
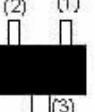
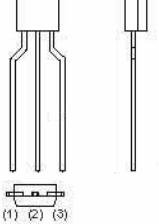
RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.

EQUIVALENT CIRCUIT



DTC143TE (SOT-523)	DTC143TUA (SOT-323)
 1.IN 2.GND 3.OUT	 1.IN 2.GND 3.OUT
Addreviated symbol : 03	Addreviated symbol : 03
DTC143TM (SOT-723)	DTC143TCA (SOT-23)
 1.IN 2.GND 3.OUT	 1.IN 2.GND 3.OUT
Addreviated symbol : 03	Addreviated symbol : 03
DTA143TSA (TO-92S)	
 1.GND 2.OUT 3.IN (1) (2) (3)	

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limits (DTC143T□)					Unit
		M	E	UA	CA	SA	
Collector-Base Voltage	$V_{(\text{BR})\text{CBO}}$			50			V
Collector-Emitter Voltage	$V_{(\text{BR})\text{CEO}}$			50			V
Emitter-Base Voltage	$V_{(\text{BR})\text{EBO}}$			5			mA
Collector Current	I_C			100			
Collector Dissipation	P_C	100	150	200	300		mW
Junction & Storage temperature	T_J, T_{STG}	150, -55~150					°C

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	50	-	-	V	$I_C=50\mu\text{A}$
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	50	-	-	V	$I_C=1\text{mA}$
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	5	-	-	V	$I_E=50\mu\text{A}$
Collector cut-off current	I_{CBO}	-	-	0.5	μA	$V_{\text{CB}}=50\text{V}$
Emitter cut-off current	I_{EBO}	-	-	0.5	μA	$V_{\text{EB}}=4\text{V}$
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	-	-	0.3	V	$I_C=5\text{mA}, I_B=0.25\text{mA}$
DC current transfer ratio	h_{FE}	100	-	600		$V_{\text{CE}}=5\text{V}, I_C=1\text{mA}$
Input resistance	R_i	3.29	4.7	6.11	$\text{k}\Omega$	
Transition frequency	f_T	-	250	-	MHz	$V_o=10\text{V}, I_o=5\text{mA}, f=100\text{MHz}$

CHARACTERISTIC CURVES

